Distributed by:

JAMECO

ELECTRONICS

www.Jameco.com + 1-800-831-4242

The content and copyrights of the attached material are the property of its owner.

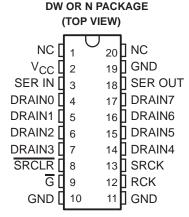
Jameco Part Number 2035258

- Low r_{DS(on)} . . . 5 Ω
- Avalanche Energy . . . 30 mJ
- Eight Power DMOS-Transistor Outputs of 150-mA Continuous Current
- 500-mA Typical Current-Limiting Capability
- Output Clamp Voltage . . . 50 V
- Enhanced Cascading for Multiple Stages
- All Registers Cleared With Single Input
- Low Power Consumption

description

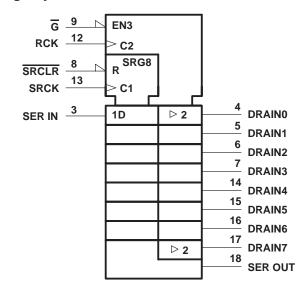
The TPIC6B596 is a monolithic, high-voltage, medium-current power 8-bit shift register designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads.

This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage registers on the rising edge of the shift-register clock (SRCK) and the register clock (RCK), respectively. The storage register transfers data to the output buffer when shift-register clear (\overline{SRCLR}) is high. When \overline{SRCLR} is low, all registers in the device are cleared. When output enable (\overline{G}) is held high, all data in the output buffers is held low and all drain outputs are off. When \overline{G} is held low, data from the storage register is transparent to the output buffers. When data in the output buffers is low, the DMOStransistor outputs are off. When data is high, the



NC - No internal connection

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

DMOS-transistor outputs have sink-current capability. The serial output (SER OUT) is clocked out of the device on the falling edge of SRCK to provide additional hold time for cascaded applications. This will provide improved performance for applications where clock signals may be skewed, devices are not located near one another, or the system must tolerate electromagnetic interference.

Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and 150-mA continuous sink-current capability. Each output provides a 500-mA typical current limit at $T_C = 25^{\circ}C$. The current limit decreases as the junction temperature increases for additional device protection.

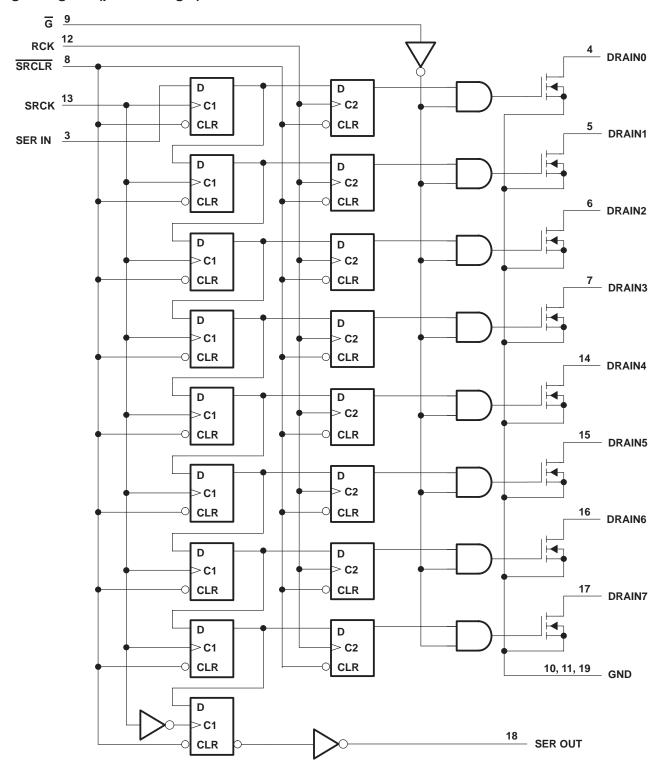
The TPIC6B596 is characterized for operation over the operating case temperature range of -40°C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

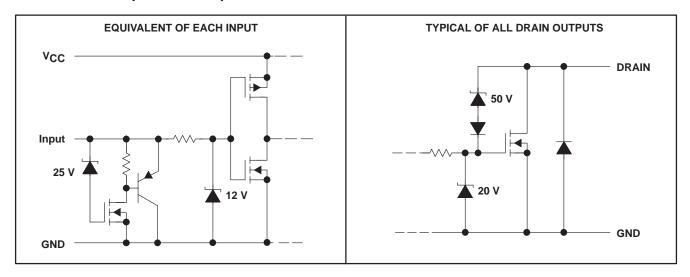


logic diagram (positive logic)





schematic of inputs and outputs



absolute maximum ratings over recommended operating case temperature range (unless otherwise noted) $\!\!\!\!\!\!^{\dagger}$

Logic supply voltage, V _{CC} (see Note 1)	7 V
Logic input voltage range, V _I	
Power DMOS drain-to-source voltage, V _{DS} (see Note 2)	
Continuous source-to-drain diode anode current	
Pulsed source-to-drain diode anode current (see Note 3)	
Pulsed drain current, each output, all outputs on, I _D , T _C = 25°C (see Note 3)	
Continuous drain current, each output, all outputs on, I_D , $T_C = 25^{\circ}C$	
Peak drain current single output, I _{DM} ,T _C = 25°C (see Note 3)	
Single-pulse avalanche energy, E _{AS} (see Figure 4)	
Avalanche current, I _{AS} (see Note 4)	
Continuous total dissipation	
Operating virtual junction temperature range, T _J	
Operating case temperature range, T _C	
Storage temperature range	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to GND.
 - 2. Each power DMOS source is internally connected to GND.
 - 3. Pulse duration \leq 100 μ s and duty cycle \leq 2%.
 - 4. DRAIN supply voltage = 15 V, starting junction temperature (T_{JS}) = 25°C, L = 200 mH, I_{AS} = 0.5 A (see Figure 4).

DISSIPATION RATING TABLE

PACKAGE	$T_C \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T _C = 25°C	T _C = 125°C POWER RATING
DW	1389 mW	11.1 mW/°C	278 mW
N	1050 mW	10.5 mW/°C	263 mW



TPIC6B596 POWER LOGIC 8-BIT SHIFT REGISTER

SLIS095A - MARCH 2000 - REVISED MAY 2005

recommended operating conditions

	N	IIN	MAX	UNIT
Logic supply voltage, V _{CC}		4.5	5.5	V
High-level input voltage, V _{IH}	0.85	VCC		V
Low-level input voltage, V _{IL}			0.15 V _{CC}	V
Pulsed drain output current, $T_C = 25^{\circ}C$, $V_{CC} = 5$ V (see Notes 3 and 5)	- 5	500	500	mA
Setup time, SER IN high before SRCK↑, t _{SU} (see Figure 2)		15		ns
Hold time, SER IN high after SRCK↑, th (see Figure 2)		15		ns
Pulse duration, t _W (see Figure 2)		40		ns
Operating case temperature, T _C	-	40	125	°C

NOTES: 3. Pulse duration \leq 100 μ s and duty cycle \leq 2%.

5. Technique should limit $T_J - T_C$ to 10°C maximum.

electrical characteristics, V_{CC} = 5 V, T_{C} = 25°C (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	MIN	TYP	MAX	UNIT	
V(BR)DSX	Drain-to-source breakdown voltage	$I_D = 1 \text{ mA}$		50			V	
V _{SD}	Source-to-drain diode forward voltage	IF = 100 mA			0.85	1	٧	
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	High-level output voltage,	$I_{OH} = -20 \mu A, V_{CC} = 4.5 V$		4.4	4.49		V	
VOH	SER OUT	$I_{OH} = -4 \text{ mA}, V_{CC} = 4.5 \text{ V}$		4	4.2		V	
V/	Low-level output voltage,	$I_{OL} = 20 \mu A$, $V_{CC} = 4.5 V$			0.005	0.1	V	
VOL	SER OUT	$I_{OL} = 4 \text{ mA}, V_{CC} = 4.5 \text{ V}$			0.3	0.5	V	
lн	High-level input current	V _C C = 5.5 V, V _I = V _C C				1	μΑ	
I _I L	Low-level input current	$V_{CC} = 5.5 \text{ V}, V_{I} = 0$				-1	μΑ	
		V 55V	All outputs off		20	100		
lcc	Logic supply current	V _{CC} = 5.5 V	All outputs on		150	300	300 μA	
ICC(FRQ)	Logic supply current at frequency	fSRCK = 5 MHz, C _L = 30 pF, All outputs off, See Figures	fSRCK = 5 MHz, C _L = 30 pF, All outputs off, See Figures 2 and 6		0.4	5	mA	
I _N	Nominal current	$V_{DS(on)} = 0.5 \text{ V},$ $I_{N} = I_{D}, T_{C} = 85^{\circ}C$	See Notes 5, 6, and 7		90		mA	
	Off state due in comment	$V_{DS} = 40 \text{ V}, V_{CC} = 5.5 \text{ V}$			0.1	5	^	
IDSX	Off-state drain current	$V_{DS} = 40 \text{ V}, V_{CC} = 5.5 \text{ V},$	T _C = 125°C		0.15	8	μΑ	
		$I_D = 100 \text{ mA}, V_{CC} = 4.5 \text{ V}$			4.2	5.7		
rDS(on)	Static drain-source on-state resistance	$I_D = 100 \text{ mA}, T_C = 125^{\circ}\text{C}, \\ V_{CC} = 4.5 \text{ V}$	See Notes 5 and 6 and Figures 7 and 8		6.8	9.5	Ω	
		$I_D = 350 \text{ mA}, V_{CC} = 4.5 \text{ V}$			5.5	8		

NOTES: 5. Technique should limit T_J – T_C to 10°C maximum.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at $T_C = 85^{\circ}C$.



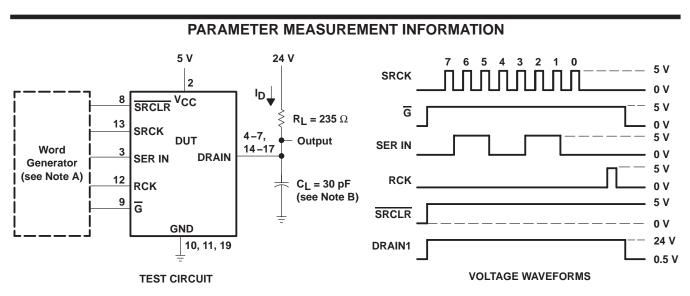
switching characteristics, $V_{CC} = 5 \text{ V}$, $T_{C} = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
^t PLH	Propagation delay time, low-to-high-level output from \overline{G}		150		ns
tPHL	Propagation delay time, high-to-low-level output from \overline{G}	$C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$	90		ns
t _r	Rise time, drain output	See Figures 1, 2, and 9	200		ns
tf	Fall time, drain output		200		ns
^t pd	Propagation delay time, SRCK↓ to SEROUT	$C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$ See Figure 2	15		ns
f(SRCK)	Serial clock frequency	$C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$ See Note 8		10	MHz
ta	Reverse-recovery-current rise time	$I_F = 100 \text{ mA}, \qquad di/dt = 20 \text{ A/}\mu\text{s},$	100		
t _{rr}	Reverse-recovery time	See Notes 5 and 6 and Figure 3	300		ns

- NOTES: 5. Technique should limit T_J T_C to 10°C maximum.
 - 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
 - 8. This is the maximum serial clock frequency assuming cascaded operation where serial data is passed from one stage to a second stage. The clock period allows for SRCK → SEROUT propagation delay and setup time plus some timing margin.

thermal resistance

PARAMETER			TEST CONDITIONS	MIN	MAX	UNIT
D. Thermal resistance in estimate eachiest	DW package	All 8 outputs with equal power		90	°C/W	
$R_{\theta JA}$	Thermal resistance, junction-to-ambient	N package	Ali o outputs with equal power		95	C/VV

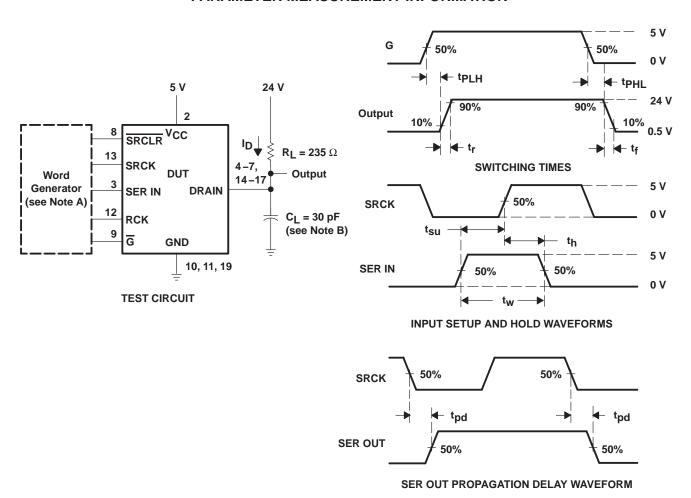


NOTES: A. The word generator has the following characteristics: $t_{\text{f}} \le 10$ ns, $t_{\text{f}} \le 10$ ns, $t_{\text{W}} = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_{\text{O}} = 50~\Omega$.

B. CL includes probe and jig capacitance.

Figure 1. Resistive-Load Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

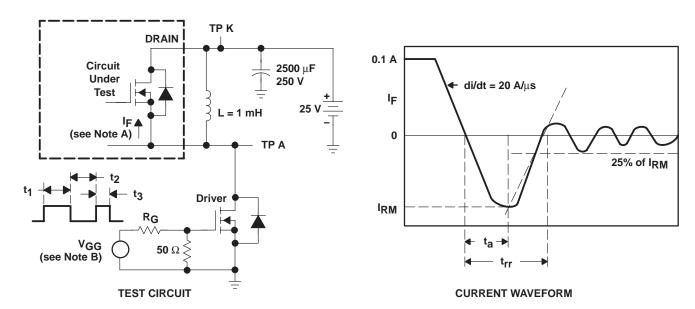


NOTES: A. The word generator has the following characteristics: $t_{\Gamma} \le 10$ ns, $t_{W} = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_{O} = 50~\Omega$.

B. CL includes probe and jig capacitance.

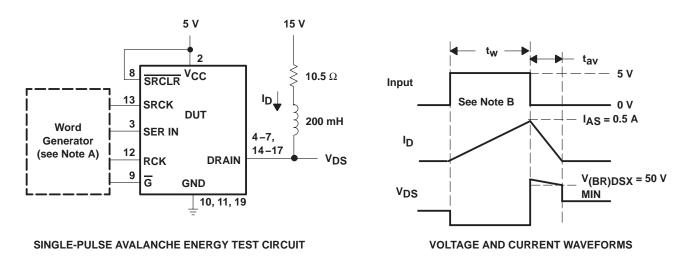
Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
 - B. The V_{GG} amplitude and R_{G} are adjusted for di/dt = 20 A/ μ s. A V_{GG} double-pulse train is used to set I_{F} = 0.1 A, where t_{1} = 10 μ s, t_{2} = 7 μ s, and t_{3} = 3 μ s.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode

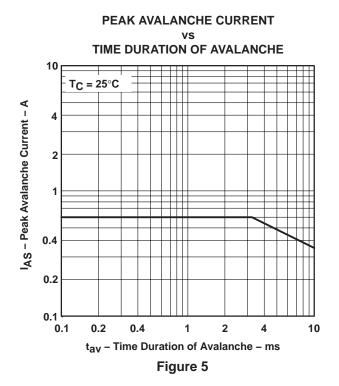


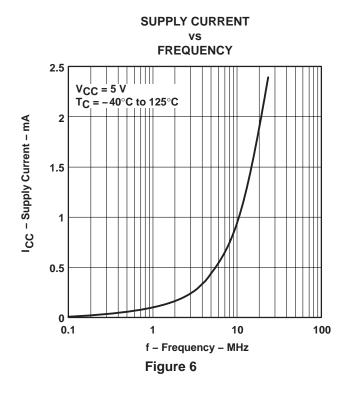
- NOTES: A. The word generator has the following characteristics: $t_{\Gamma} \le 10$ ns, $t_{f} \le 10$ ns, $t_{O} = 50 \Omega$.
 - B. Input pulse duration, t_W , is increased until peak current $I_{AS} = 0.5$ A. Energy test level is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 30$ mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms



TYPICAL CHARACTERISTICS





DRAIN-TO-SOURCE ON-STATE RESISTANCE vs

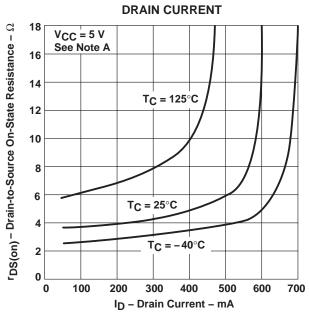
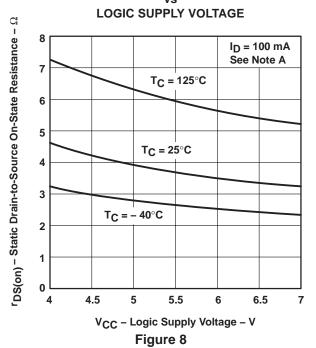


Figure 7

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE vs



SLIS095A - MARCH 2000 - REVISED MAY 2005

TYPICAL CHARACTERISTICS

SWITCHING TIME vs CASE TEMPERATURE

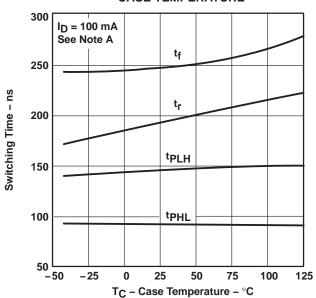
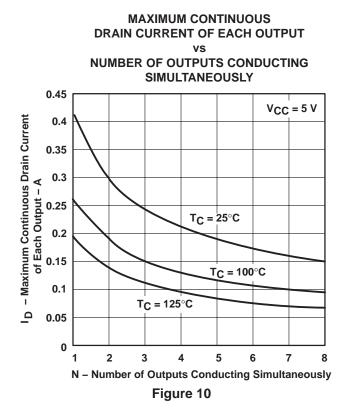
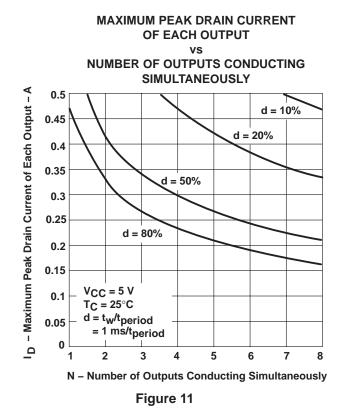


Figure 9

NOTE A: Technique should limit $T_J - T_C$ to 10°C maximum.

THERMAL INFORMATION





Revision History

DATE	REV	PAGE	SECTION	DESCRIPTION
5/18/05	Α	5	Figure 1	Changed SRCLR timing diagram
3/2000	*			Original reversion

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.





.com 29-May-2007

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPIC6B596DW	ACTIVE	SOIC	DW	20	25	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6B596DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6B596DWR	ACTIVE	SOIC	DW	20	2000	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6B596DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6B596N	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

DW (R-PDSO-G20)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products Amplifiers amplifier.ti.com Data Converters dataconverter.ti.com DSP dsp.ti.com Clocks and Timers www.ti.com/clocks Interface interface.ti.com Logic logic.ti.com Power Mgmt power.ti.com Microcontrollers microcontroller.ti.com www.ti-rfid.com RF/IF and ZigBee® Solutions www.ti.com/lprf

Applications	
Audio	www.ti.com/audio
Automotive	www.ti.com/automotive
Broadband	www.ti.com/broadband
Digital Control	www.ti.com/digitalcontrol
Medical	www.ti.com/medical
Military	www.ti.com/military
Optical Networking	www.ti.com/opticalnetwork
Security	www.ti.com/security
Telephony	www.ti.com/telephony
Video & Imaging	www.ti.com/video
Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2008, Texas Instruments Incorporated